BR2SB1198MCQ

Rev.A Apr.-2023

DATA SHEET

/ Descriptions

VRW5606 ꓡ SQS ᛧ Silicon PNP transistor in a SOT23-3 Plastic Package.

/ Features

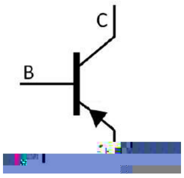
EU5VG4:;5PFT AEC-Q101

High breakdown, low $V_{CE(sat)}$,complements the BR2SD1782MCQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

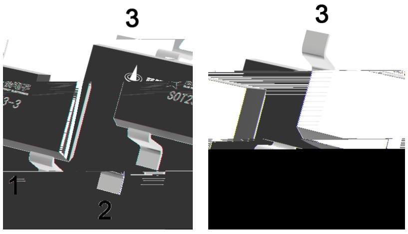
/ Applications

Medium power amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



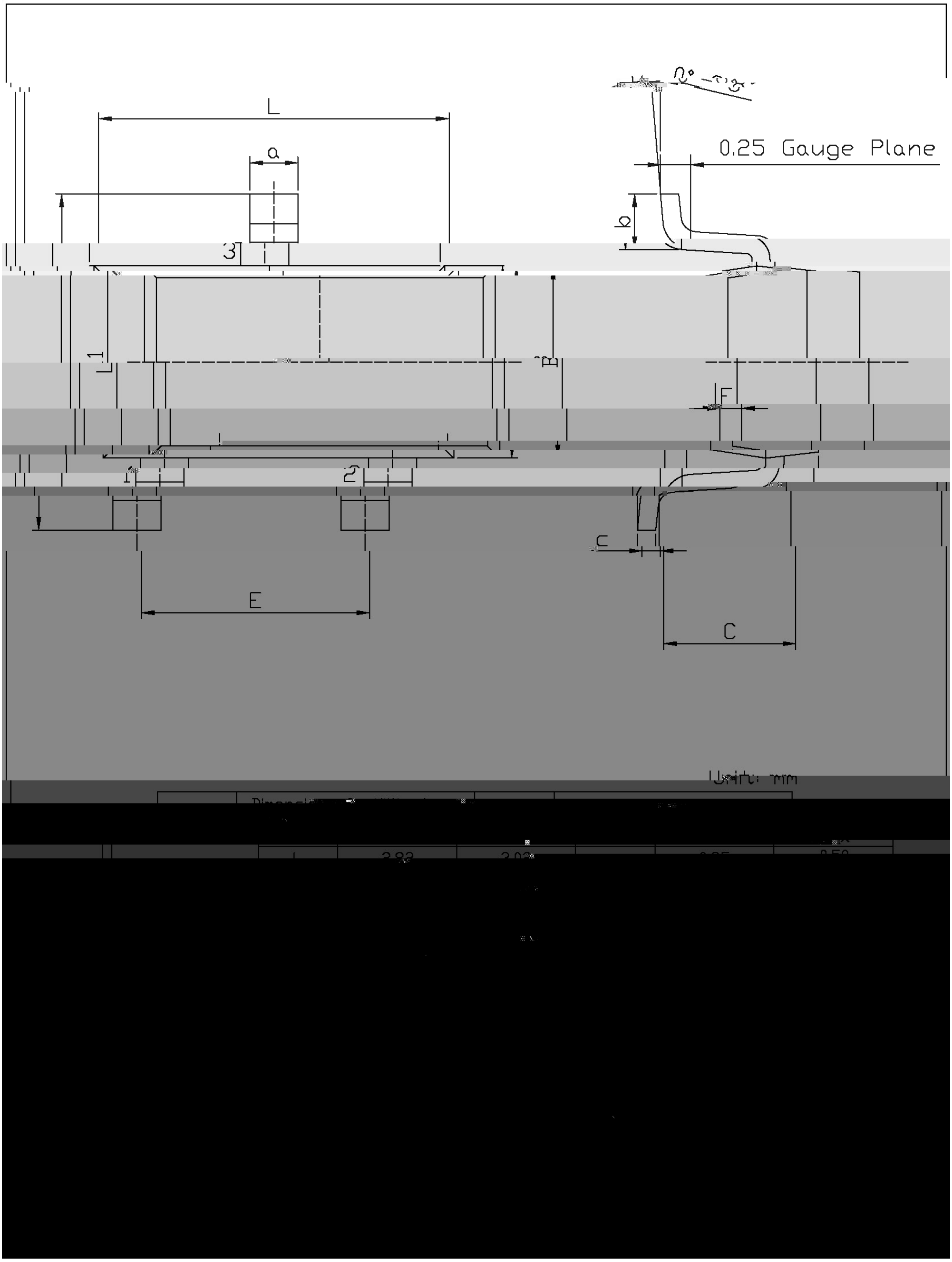
PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Q	R
h_{FE} Range	120~270	180~390
Marking	QAKQ	QAKR

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA

/ Package Dimensions



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/ Marking Instructions

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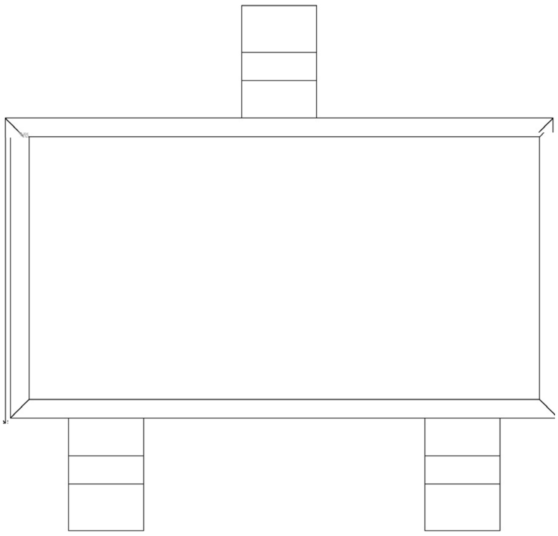
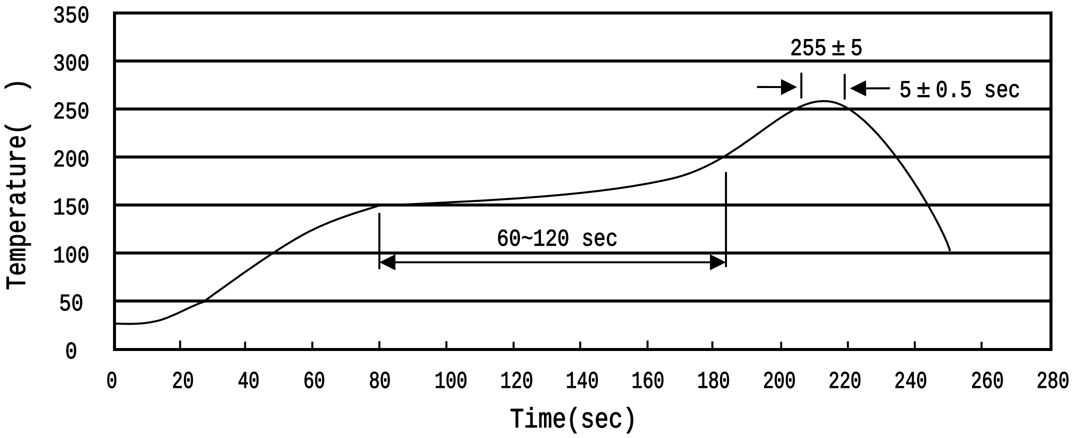


( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



ب

1 أ 150 200 ڑ 60 120sec;

2 255±5 ڑ ٨ 5±0.5sec;

3 ٢ ھ 2 10 /sec.

Note:

1.Preheating:150~200 , Time:60~120sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 ڑ 10±1 sec.

Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

ㄴ / REEL

Package Type	Units					Dimension (unit mm^3)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT23-3	3,000	10	30,000	4	120,000	7 ×8	210×205×205	445×230×435

/ Notices